

Figure 1. SIMS stack of Si doped Ga₂O₃ by suboxide source with different disilane flow rates. Si concentration of $3 \times 10^{16} \text{cm}^{-3}$ to $1 \times 10^{19} \text{cm}^{-3}$ has been achieved.

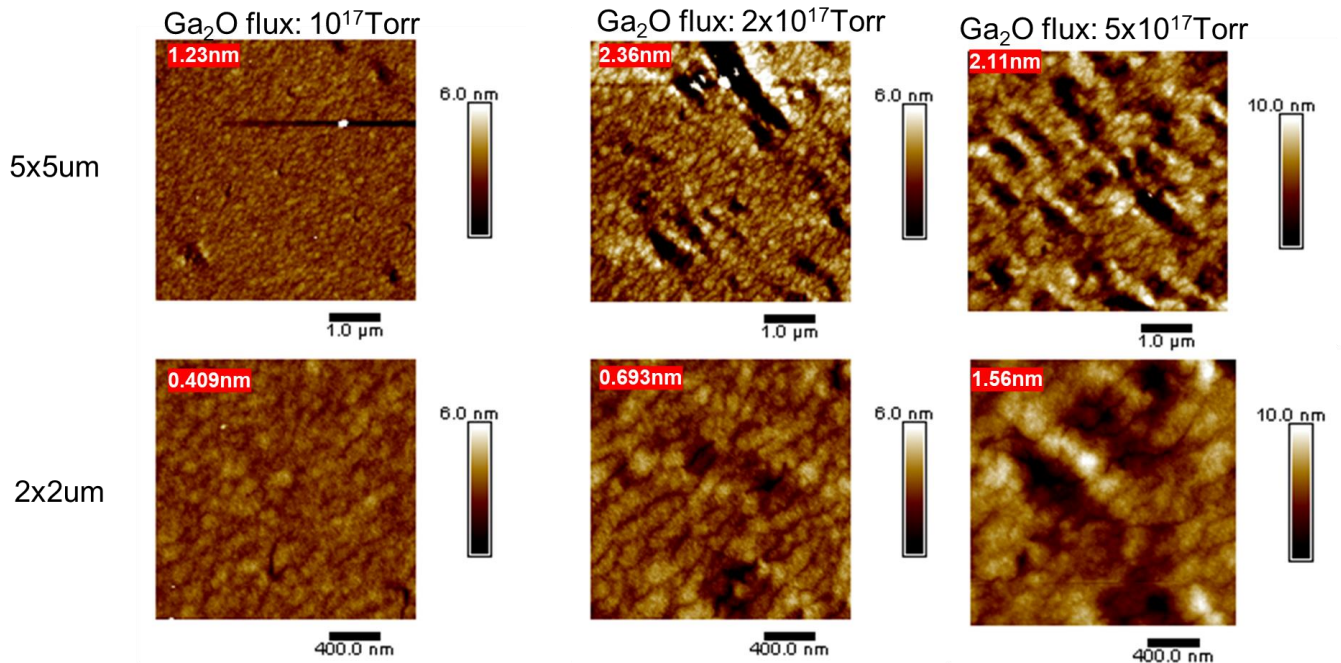


Figure 2. AFM images of Ga₂O₃ surface morphology growth by different sub-oxide fluxes.